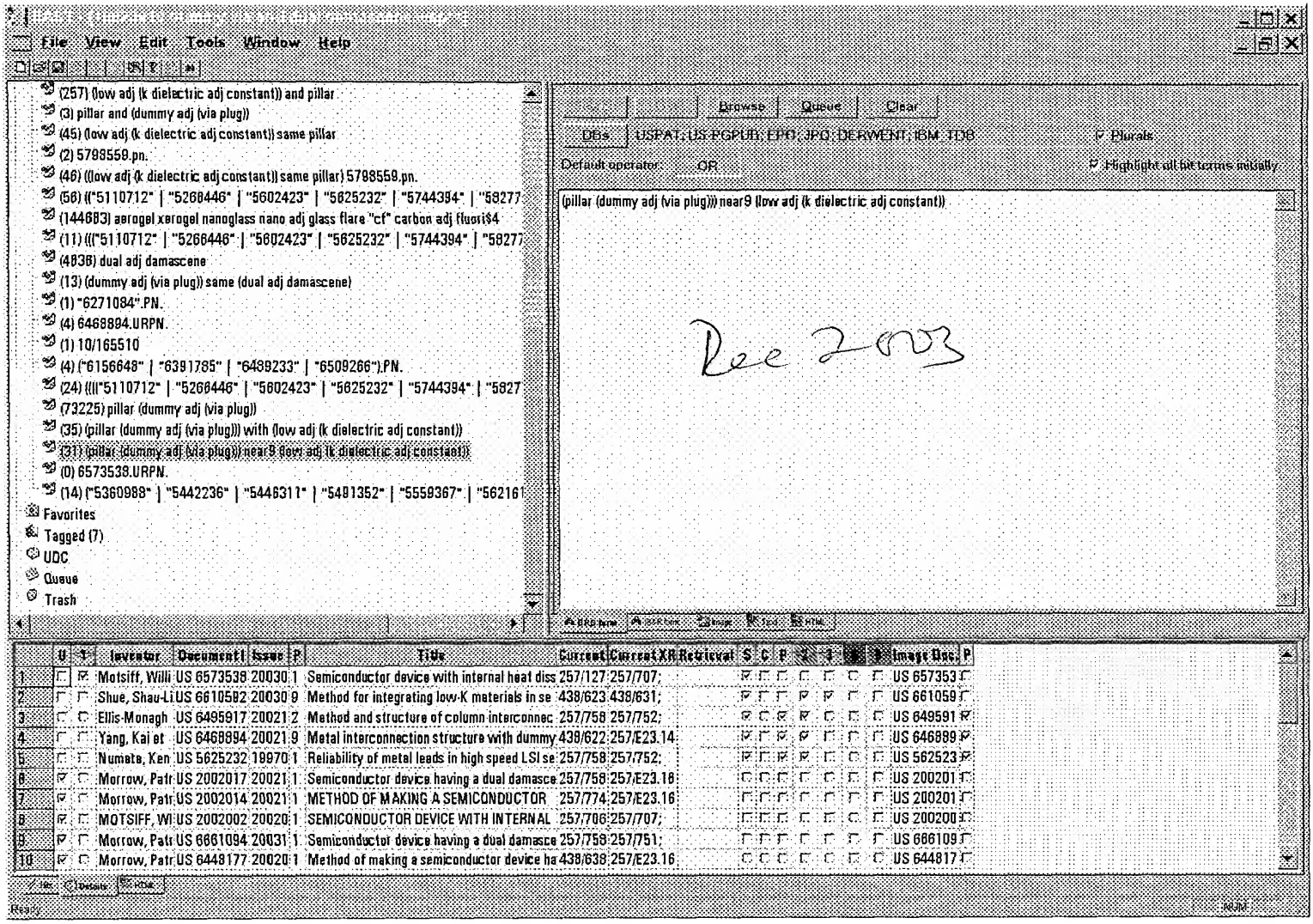
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(257) (low adj (k dielectric adj constant)) and pillar
(3) pillar and (dummy adj (via plug))
(45) (low adj (k dielectric adj constant)) same pillar
(2) 5798559.pn.
(46) ((low adj (k dielectric adj constant)) same pillar) 5798559.pn.
(56) (("5110712" | "5266446" | "5602423" | "5625232" | "5744394" | "58277
(144683) aerogel xerogel nanoglass nano adj glass flare "cf" carbon adj fluori$4
(11) ((("5110712" | "5266446" | "5602423" | "5625232" | "5744394" | "58277
(4838) dual adj damascene
(13) (dummy adj (via plug)) same (dual adj damascene)
(1) "6271084".PN.
(4) 6468894.URPN.
(1) 10/165510
(4) ("6156648" | "6391785" | "6489233" | "6509266").PN.
(24) ((("5110712" | "5266446" | "5602423" | "5625232" | "5744394" | "5827
(73225) pillar (dummy adj (via plug))
(35) (pillar (dummy adj (via plug))) with (low adj (k dielectric adj constant))
(31) (pillar (dummy adj (via plug))) near9 (low adj (k dielectric adj constant))
(0) 6573538.URPN.
(14) ("5360988" | "5442236" | "5446311" | "5481352" | "5559367" | "56216
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(pillar (dummy adj (via plug))) near9 (low adj (k dielectric adj constant))
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4 Yang, Kai et US 6468894 20021 9 Metal interconnection structure with dummy 438/622 257/E23.14 US 646889
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9 Morrow, Patr US 6661094 20031 1 Semiconductor device having a dual damasce 257/758 257/751; US 666109
10 Morrow, Patr US 6448177 20020 1 Method of making a semiconductor device ha 438/638 257/E23.16 US 644817
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